

Hosted Meeting

A. The Institute of Electronics, Information and Communication Engineering (IEICE)

1. "The current status of InN-including Materials and its Future" as 1st Workshop "Summer meeting of Materials and Devices in Expert Committee on Next-Generation Nano-Technology (2nd Period)" Tokyo, Jun. 30, 2006
2. "2nd The current status of InN-including Materials and its Future" as 2nd Workshop "Summer meeting of Materials and Devices in Expert Committee on Next-Generation Nano-Technology (3rd Period) " Tokyo, Jun. 27, 2008

B. Workshop of Research Collaboration, Research of Institute for Materials Research (IMR)

1. Kick-Off Meeting on High-Quality Crystal Growth of Nitride Semiconductors and its Applications (Institute of Multidisciplinary Research for Advanced Materials, Tohoku Univ., Sendai, Jul. 31, 2009).
2. 2nd Workshop on High-Quality Crystal Growth of Nitride Semiconductors and its Applications (IMR, Tohoku Univ., Sendai, Dec. 22-23, 2009).
3. 3rd Workshop on High-Quality Crystal Growth of Nitride Semiconductors and its Applications (IMR, Tohoku Univ., Sendai, Oct. 25-26, 2010).
4. 4th Workshop on High-Quality Crystal Growth of Nitride Semiconductors and its Applications (IMR, Tohoku Univ., Sendai, Jan. 17-18, 2011).
5. 5th Workshop on High-Quality Crystal Growth of Nitride Semiconductors and its Applications (IMR, Tohoku Univ., Sendai, Aug. 8-9, 2012).
6. 6th Workshop on High-Quality Crystal Growth of Nitride Semiconductors and its Applications (IMR, Tohoku Univ., Sendai, Dec. 26-27, 2012).

C. International Workshop

1. 1st Intensive Discussion on Growth of Nitride Semiconductors (IDGN)
(Tohoku Univ., Sendai, Oct. 22-23, 2012).
2. 2nd IDGN (Tohoku Univ., Sendai, Oct. 29-31, 2014).
3. 3rd IDGN (Tohoku Univ., Sendai, Jan. 16-18, 2017).
4. 4th IDGN (Tohoku Univ., Sendai, Nov. 18-20, 2018).

D. Colloquium

1. 1st Colloquium on Crystals
Lecturer : Prof. Tsutomu Nakanishi, Nagoya University
Topics : "Development of Electron Source with High Luminance and High Spin-Polarization"
Schedule : 10:00~12:00, Jun. 26, 2008
Place : Seminar Room 1, Institute for Materials Research (IMR), Tohoku Univ., Sendai

2. 2nd Colloquium on Crystals

Lecturer : Visiting Prof. Michio Kadota, Micro System Integration Center, Tohoku Univ.

Topics : "Surface-Acoustic-Wave Devices of Nitride Semiconductors"

Schedule : 平成 25 年 9 月 6 日 (金) 10:00~12:00

Place : Seminar Room, IMR, Tohoku Univ., Sendai

3. 3rd Colloquium on Crystals

Lecturer : Assoc. Prof. Tomoki Abe, Totori University

Topics : "Epitaxial Growth of N-Doped ZnO and its Conduction-Type Control"

Schedule : 13:30~15:40, Jun. 24, 2014

Place : Audiovisual Room, IMR, Tohoku Univ., Sendai

4. 4th Colloquium on Crystals

Lecturer : Prof. Michał Boćkowski, Institute of High Pressure Physics, Poland

Topics : "Crystal Growth of Bulk GaN"

Schedule : 13:30~14:30, Jan. 7, 2016

Place : Audiovisual Room, IMR, Tohoku Univ., Sendai

5. 5th Colloquium on Crystals

Lecturer: Prof. Zlatko Sitar, North Carolina State University, USA

Topics: "Control of Surface Kinetics During the Growth of III-Nitrides on Native Substrates"

Schedule: 13:00~15:00, Apr. 6, 2017

Place: Big Hall, IMR, Tohoku Univ., Sendai

6. 6th Colloquium on Crystals

Lecturer: Prof. Tohru Kachi,

Institute of Materials and Systems for Sustainability, Nagoya University

Toyota Advanced Power Electronics Industry-Academia Collaborative Chair

Topics: "Current Status and Future on GaN Power Devices for Automobile Applications"

Schedule: 14:00~16:00, Aug. 24, 2017

Place: Seminar Room 1, IMR, Tohoku Univ., Sendai